





100V PNP MEDIUM POWER TRANSISTOR IN SOT23

Features

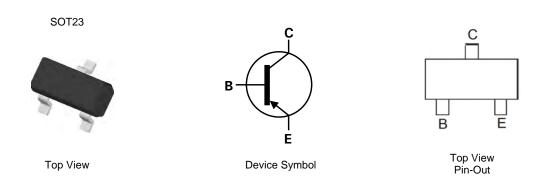
- BV_{CEO} > -100V
- Maximum Continuous Collector Current I_C = -1A
- V_{CE(sat)} < -220mV @ -1A
- R_{CE(sat)} = 150mΩ
- 7V reverse blocking voltage
- High peak current
- Complementary part number ZXTN25100CFH
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- UL Flammability Rating 94V-0
- Case material: molded Plastic.
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

Applications

- MOSFET and IGBT gat driving
- DC DC converters
- Motor drive
- High side driver



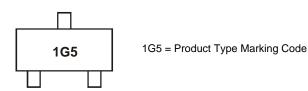
Ordering Information (Note 4)

Ī	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXTP25100CFHTA	1G5	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

Marking Information







Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-115	V
Collector-Emitter Voltage	V _{CEO}	-100	٧
Emitter-collector voltage (reverse blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current (Note 5)	Ic	-1	Α
Base Current	Ι _Β	-500	mA
Peak Pulse Current	I _{CM}	-3	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.73	W	
Collector Power Dissipation	(Note 6)	Б	1.05		
Collector Fower Dissipation	(Note 7)	P_{D}	1.25	VV	
	(Note 8)		1.81		
	(Note 5)		171	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	D	119		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	100		
	(Note 8)		69		
Thermal Resistance, Junction to Leads	(Note 9)	$R_{ heta JL}$	75.25	°C/W	
Operating and Storage Temperature Range	T_J,T_STG	-55 to +150	°C		

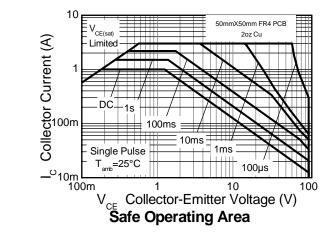
Notes:

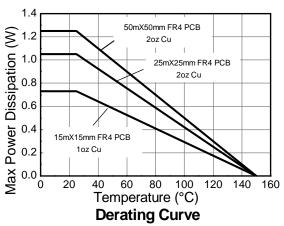
- 5. For the device mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1oz copper in still air condition; 6. Mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 2oz copper in still air condition 7. Mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 2oz copper in still air condition

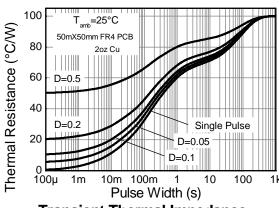
- 8. As Note 7 above, measured at t < 5 secs.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).

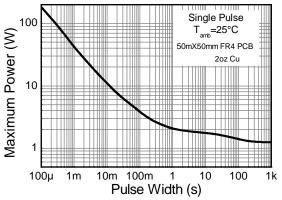


Thermal Characteristics @TA = 25°C unless otherwise specified









Transient Thermal Impedance

Pulse Power Dissipation





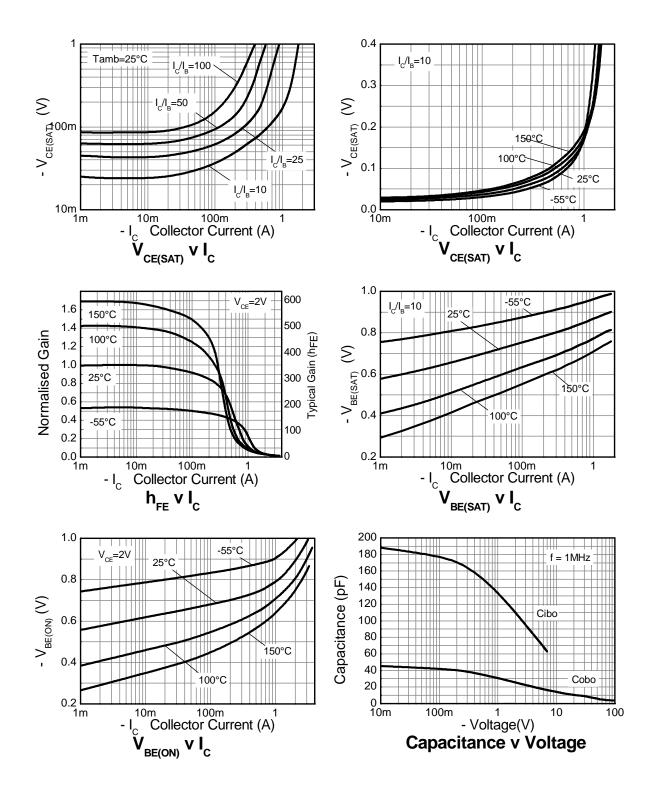
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-115	-180	-	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-100	-140	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.4	-	V	$I_E = -100 \mu A$
Emitter-Base Breakdown Voltage	BV _{ECX}	-7	-8.3	1	V	$I_E = -100\mu A$, $R_{BC} < 1k\Omega$ or
5 W 5 5 11 1/1		_				-0.25 < V _{BC} < 0.25V
Emitter-Base Breakdown Voltage	BV _{ECO}	-7	-8.8	-	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	Ісво	-	< -1	-50	nA	V _{CB} = -115V
Condition Bade Gatem Carrotte		-	-	-0.5	μA	V _{CB} = -115V, T _{amb} = 100°C
Collector-Emitter Cutoff Current	I _{CEX}	_	_	-100	nA	$V_{CE} = -90V$, $R_{BE} < 1k\Omega$ or
	ICEX					-0.25V < V _{BE} < 1V
Emitter-Base Cutoff Current	I _{EBO}	-	< -1	-50	nA	V _{EB} = -5.6V
		200	350	500		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 10)	h	180	320	-		$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 10)	h _{FE} 110 190 - 20 35 -	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$				
		20	35	-		$I_C = -1A$, $V_{CE} = -2V$
	V _{CE(sat)}	-	-140	-210	mV	I _C = - 100mA, I _B = -1mA
Callactor Emitter Saturation Voltage (Note 10)		-	-80	-110		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)		-	-180	-310		I _C = - 500mA, I _B = -20mA
		-	-150	-220		I _C = - 1A, I _B = -100mA
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	-849	-950	mV	I _C = -1A, I _B = -100mA
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(on)}$	-	-790	-900	mV	$I_C = -1A$, $V_{CE} = -2V$
Output Capacitance	C _{obo}	-	14.1	20	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	-	180	-	MHz	V _{CE} = -15V, I _C = -20mA, f = 100MHz
Delay Time	t _(d)	-	15.8	-	ns	
Rise Time	t _(r)	-	41	-	ns	$V_{CC} = -10V, I_{C} = -500mA,$
Storage Time	t _(S)	-	411	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Fall Time	t _(f)	-	89	-	ns	

Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



Typical Electrical Characteristics @T_A = 25°C unless otherwise specified

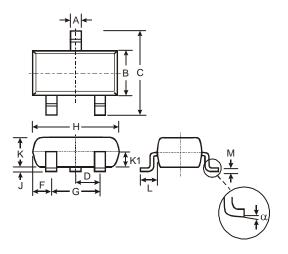






Package Outline Dimensions

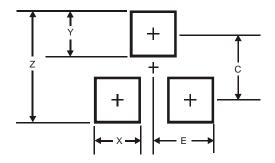
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	8.0
Υ	0.9
С	2.0
E	1.35





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